

Refine Search

Search Results -

Terms	Documents
L10 same L2	36

Database:

US Pre-Grant Publication Full-Text Database
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 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L11

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Recall Text

Clear

Interrupt

Search History

DATE: Thursday, July 22, 2004 [Printable Copy](#) [Create Case](#)

Set Name Query

side by side

Hit Count Set Name

result set

DB=USPT; PLUR=YES; OP=OR

<u>L11</u>	L10 same l2	36	<u>L11</u>
<u>L10</u>	"input/output" or "i/o"	136182	<u>L10</u>
<u>L9</u>	L8 same l1	1	<u>L9</u>
<u>L8</u>	double adj1 data adj1 rate	1169	<u>L8</u>
<u>L7</u>	L3 same l1	8	<u>L7</u>
<u>L6</u>	L3 and l1	72	<u>L6</u>
<u>L5</u>	L2 and l3	2	<u>L5</u>
<u>L4</u>	L3 same l2	0	<u>L4</u>
<u>L3</u>	ddr	2393	<u>L3</u>
<u>L2</u>	L1 near4 interface	225	<u>L2</u>
<u>L1</u>	self-test\$ or bist	7000	<u>L1</u>

END OF SEARCH HISTORY

[First Hit](#) [Fwd Refs](#)**End of Result Set**

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Print

L5: Entry 2 of 2

File: USPT

Dec 17, 2002

DOCUMENT-IDENTIFIER: US 6496429 B2

TITLE: Semiconductor memory device

Detailed Description Text (88):

In the above description, both the built-in self-test circuit and the test interface circuit are used. In the system LSI, however, only one of the test interface circuit and the built-in self-test circuit may be disposed.

Detailed Description Text (89):

When built-in self-test (BIST) circuit or test interface circuit (TIC) is alternatively used, the voltage level of repair analyzer enable signal RAen may be set fixedly by mask interconnection or the like in accordance with the use. When both the BIST circuit and test interface circuit (TIC) are used, it is sufficient to set repair analyzer enable signal RAen to the L level as a default and to set repair analyzer enable signal RAen to the H level when BIST circuit performs a test.

Detailed Description Text (93):

The present invention can be also applied to a DDR (Double Data Rate) DRAM in which data is input/output synchronously with both the rising and falling edges of a clock signal. The present invention can be also readily applied to a DDR DRAM, with the configuration in which, as data an input/output latch circuit, a latch circuit for transferring data at the rising edge of a clock signal and a latch circuit for transferring data at the falling edge of the dock signal are provided in parallel with each other and are alternately made activate.